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Tech ID: 23784

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- Etching Technique for the Fabrication of Thin (Al, In, Ga)N Layers
- Lateral Growth Method for Defect Reduction of Semipolar Nitride Films
- Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- Aluminum-cladding-free Nonpolar III-Nitride LEDs and LDs
- Defect Reduction in GaN films using in-situ SiNx Nanomask
- Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
- Transparent Mirrorless (TML) LEDs
- Optimization of Laser Bar Orientation for Nonpolar Laser Diodes
- Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices
- Growth of High-Quality, Thick, Non-Polar M-Plane GaN Films
- High-Efficiency, Mirrorless Non-Polar and Semi-Polar Light Emitting Devices
- Controlled Photoelectrochemical (PEC) Etching by Modification of Local Electrochemical Potential of Semiconductor Structure
- Technique for the Nitride Growth of Semipolar Thin Films, Heterostructures, and Semiconductor Devices
- MOCVD Growth of Planar Non-Polar M-Plane Gallium Nitride
- Methods for Fabricating III-Nitride Tunnel Junction Devices
- Contact Architectures for Tunnel Junction Devices
- Semi-polar LED/LD Devices on Relaxed Template with Misfit Dislocation at Hetero-interface
- Semipolar-Based Yellow, Green, Blue LEDs with Improved Performance
- Growth of Semipolar III-V Nitride Films with Lower Defect Density
- III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
- Cleaved Facet Edge-Emitting Laser Diodes Grown on Semipolar GaN
- Growth of High-Performance M-plane GaN Optical Devices
- Improved Anisotropic Strain Control in Semipolar Nitride Devices
- Method for Increasing GaN Substrate Area in Nitride Devices
- Limiting Strain-Relaxation in III-Nitride Heterostructures by Substrate Patterning
- Growth of Planar Semi-Polar Gallium Nitride
- Defect Reduction of Non-Polar and Semi-Polar III-Nitrides

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